



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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企业微信二维码



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Product Summary

BV _{DSS}	R _{DS(on)}	I _D T _C = +25°C
-30V	3.8mΩ @ V _{GS} = -10V	-100A
	10.0mΩ @ V _{GS} = -6V	-90A

Features

- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switch (UIS) Test in Production
- Thermally Efficient Package-Cooler Running Applications
- High Conversion Efficiency
- Low R_{DS(on)} – Minimizes On State Losses < 1.1mm Package Profile – Ideal for Thin Applications

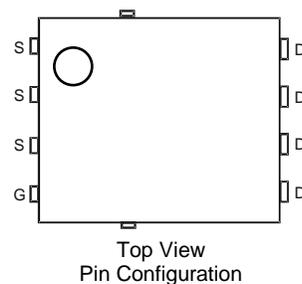
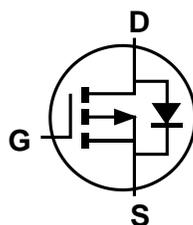
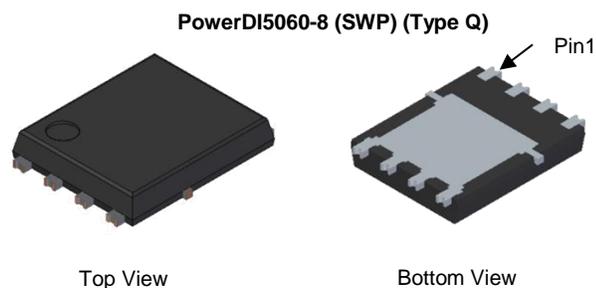
Description

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Switches

Mechanical Data

- Package: PowerDI[®]5060-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 
- Weight: 0.097 grams (Approximate)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	-30	V	
Gate-Source Voltage	V _{GSS}	±20	V	
Continuous Drain Current, V _{GS} = -10V (Note 7) (Package Limited)	I _D	T _C = +25°C	-100	A
		T _C = +100°C	-90	A
Pulsed Drain Current (380μs Pulse, Duty Cycle = 1%)	I _{DM}	-400	A	
Maximum Continuous Body Diode Forward Current (Note 6)	I _S	-4.7	A	
Pulsed Body Diode Forward Current (380μs Pulse, Duty Cycle = 1%)	I _{SM}	-400	A	
Avalanche Current, L = 0.1mH (Note 8)	I _{AS}	-69	A	
Avalanche Energy, L = 0.1mH (Note 8)	E _{AS}	241	mJ	

Thermal Characteristics

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	P _D	1.7	W	
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	Steady State	90.1	°C/W
Total Power Dissipation (Note 6)		P _D	3.4	W
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	Steady State	44	°C/W
Thermal Resistance, Junction to Case (Note 7)		R _{θJC}	1.1	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +175	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)						
Drain-Source Breakdown Voltage	BV _{DSS}	-30	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1	μA	V _{DS} = -24V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	V _{GS(th)}	-1	-2.3	-3	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(on)}	—	2.4	3.8	mΩ	V _{GS} = -10V, I _D = -20A
		—	4.6	10		V _{GS} = -6V, I _D = -20A
Diode Forward Voltage	V _{SD}	—	—	-1.2	V	V _{GS} = 0V, I _S = -1A
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C _{ISS}	—	3,775	—	pF	V _{DS} = -15V, V _{GS} = 0V f = 1MHz
Output Capacitance	C _{OSS}	—	932	—	pF	
Reverse Transfer Capacitance	C _{RSS}	—	500	—	pF	
Gate Resistance	R _g	—	21	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = -4.5V)	Q _g	—	41	—	nC	V _{DS} = -15V, V _{GS} = -10V, I _D = -20A
Total Gate Charge (V _{GS} = -10V)	Q _g	—	81	—	nC	
Gate-Source Charge	Q _{gs}	—	21.5	—	nC	
Gate-Drain Charge	Q _{gd}	—	12.7	—	nC	
Turn-On Delay Time	t _{D(on)}	—	6.9	—	ns	V _{DD} = -15V, V _{GEN} = -10V R _{GEN} = 3Ω, I _D = -20A
Turn-On Rise Time	t _R	—	4.0	—	ns	
Turn-Off Delay Time	t _{D(off)}	—	372	—	ns	
Turn-Off Fall Time	t _F	—	160	—	ns	
Reverse Recovery Time	t _{RR}	—	26.5	—	ns	I _F = -20A, di/dt = 500A/μs
Reverse Recovery Charge	Q _{RR}	—	37.3	—	nC	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - Thermal resistance from junction to soldering point (on the exposed drain pad).
 - I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

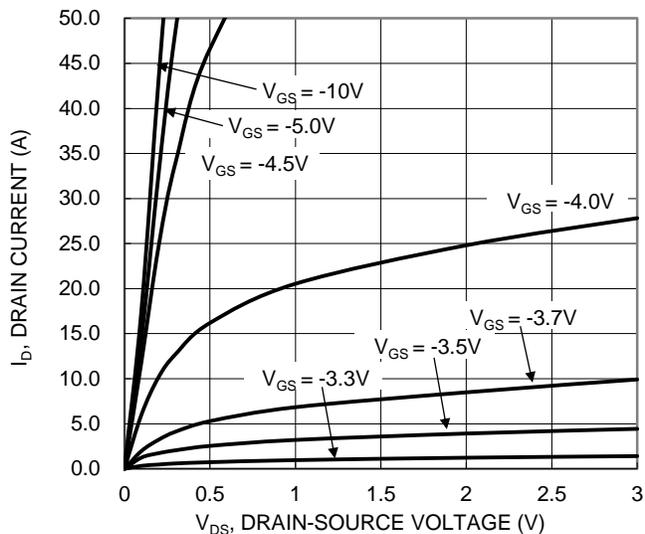


Figure 1. Typical Output Characteristic

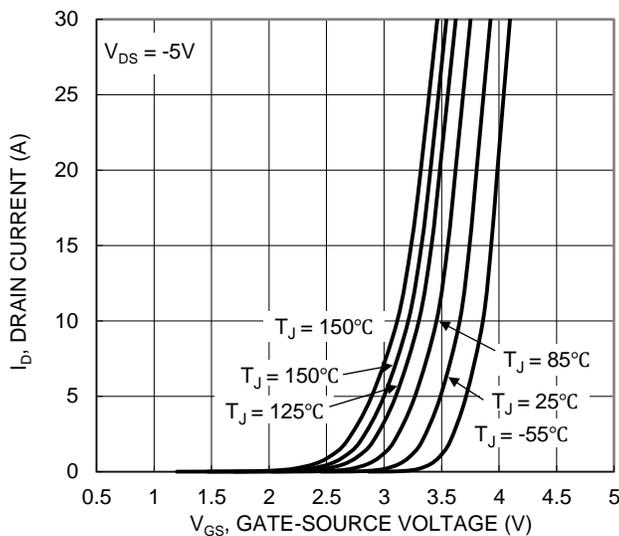


Figure 2. Typical Transfer Characteristic

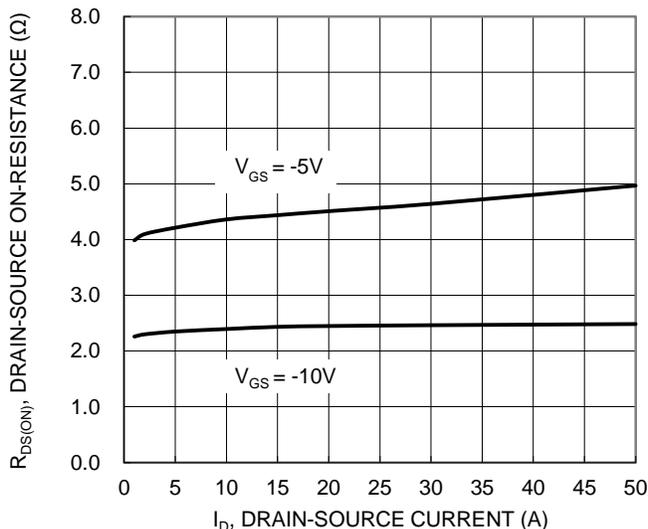


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

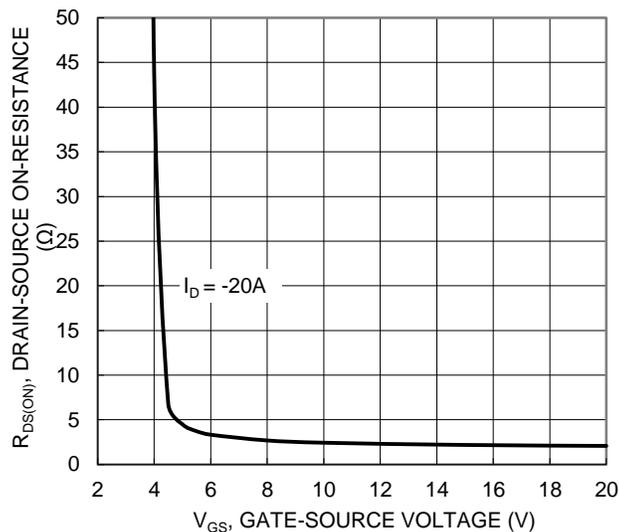


Figure 4. Typical Transfer Characteristic

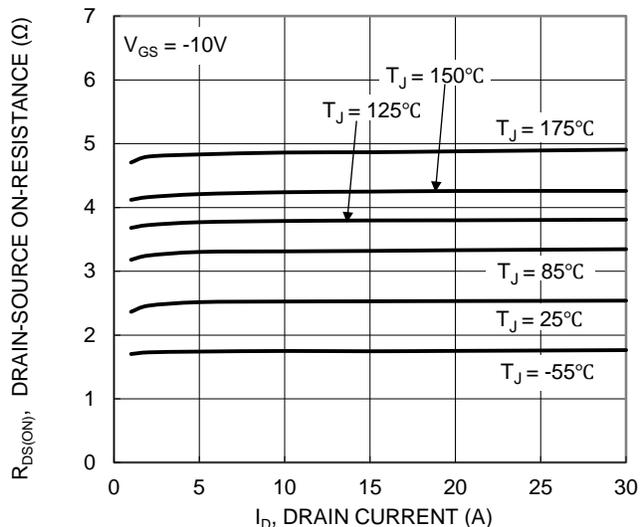


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

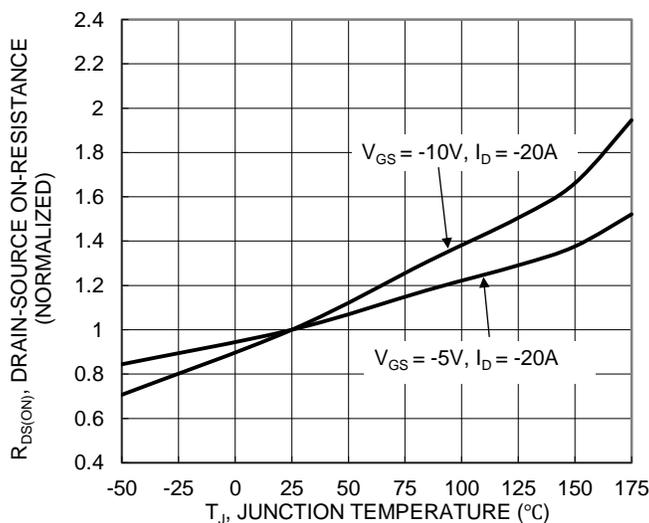


Figure 6. On-Resistance Variation with Temperature

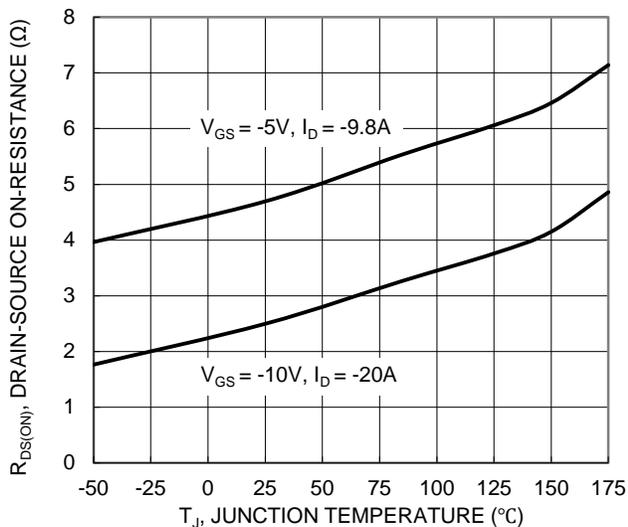


Figure 7. On-Resistance Variation with Temperature

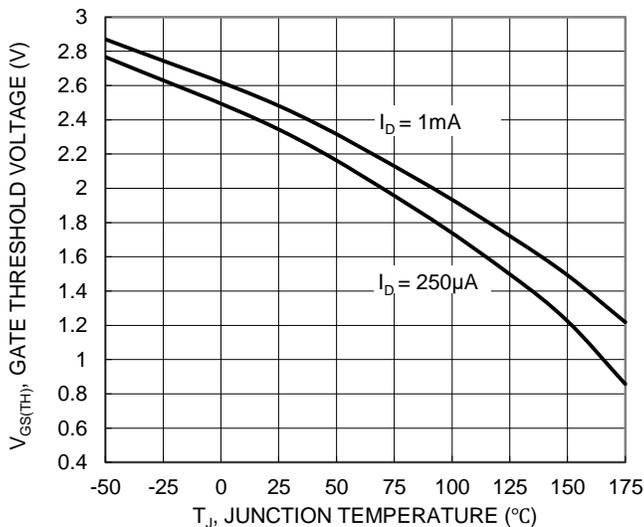


Figure 8. Gate Threshold Variation vs. Junction Temperature

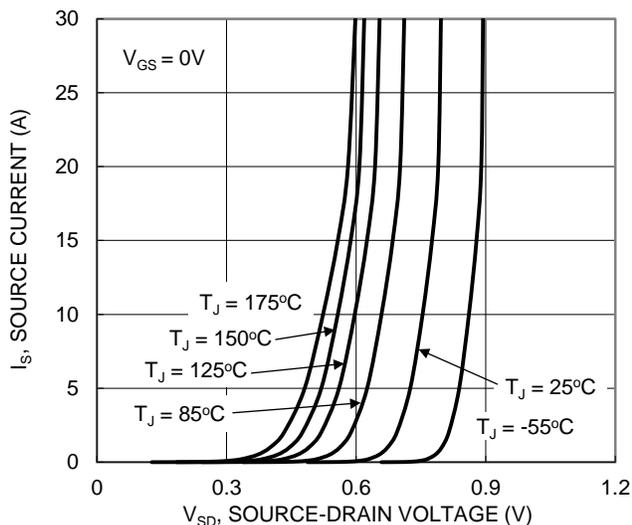


Figure 9. Diode Forward Voltage vs. Current

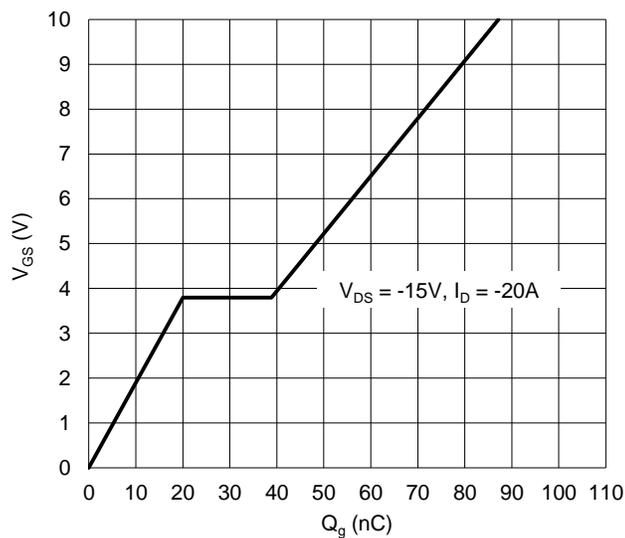


Figure 10. Gate Charge

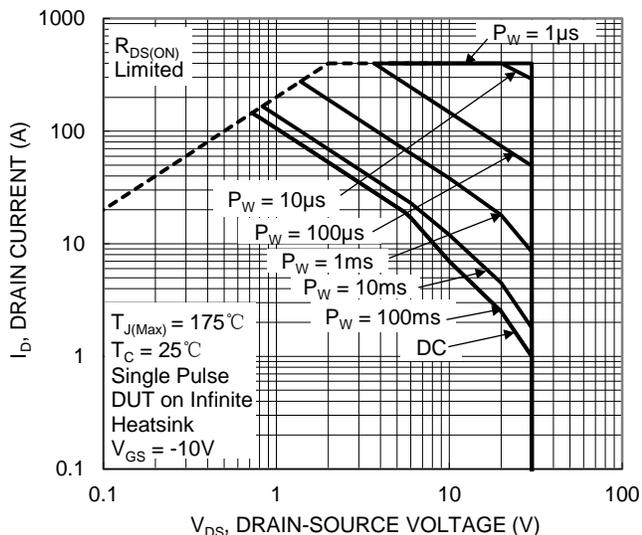


Figure 11. SOA, Safe Operation Area

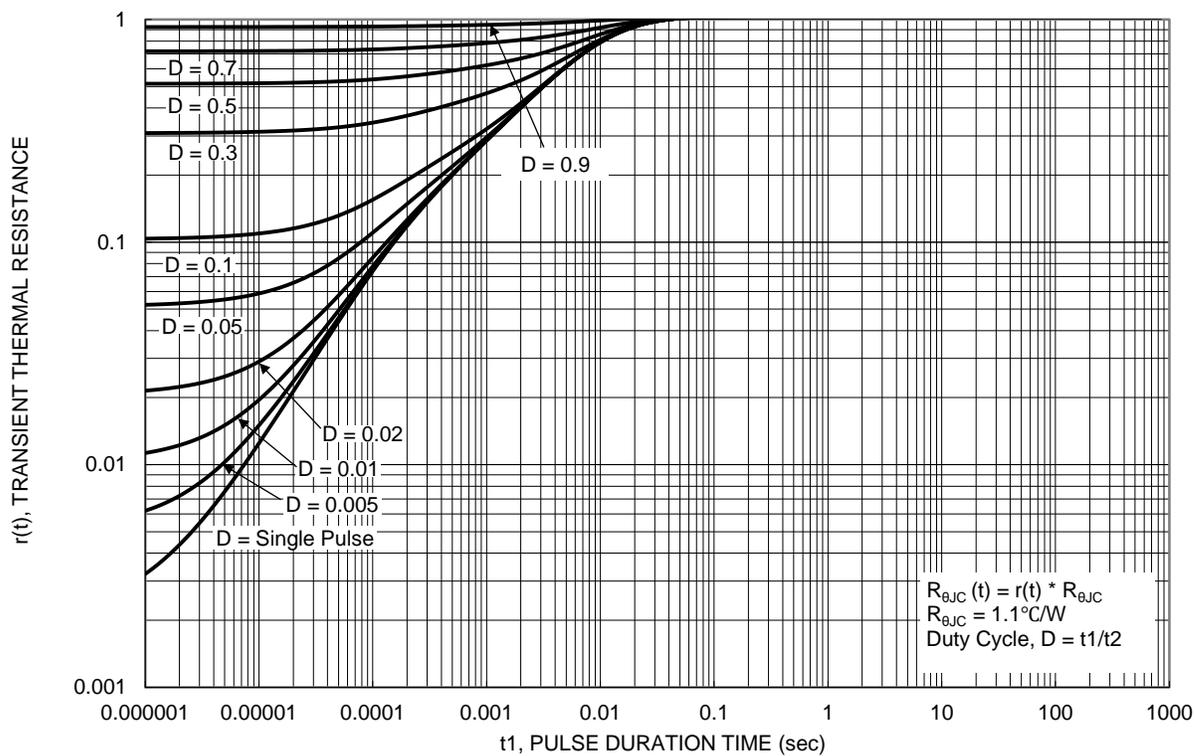
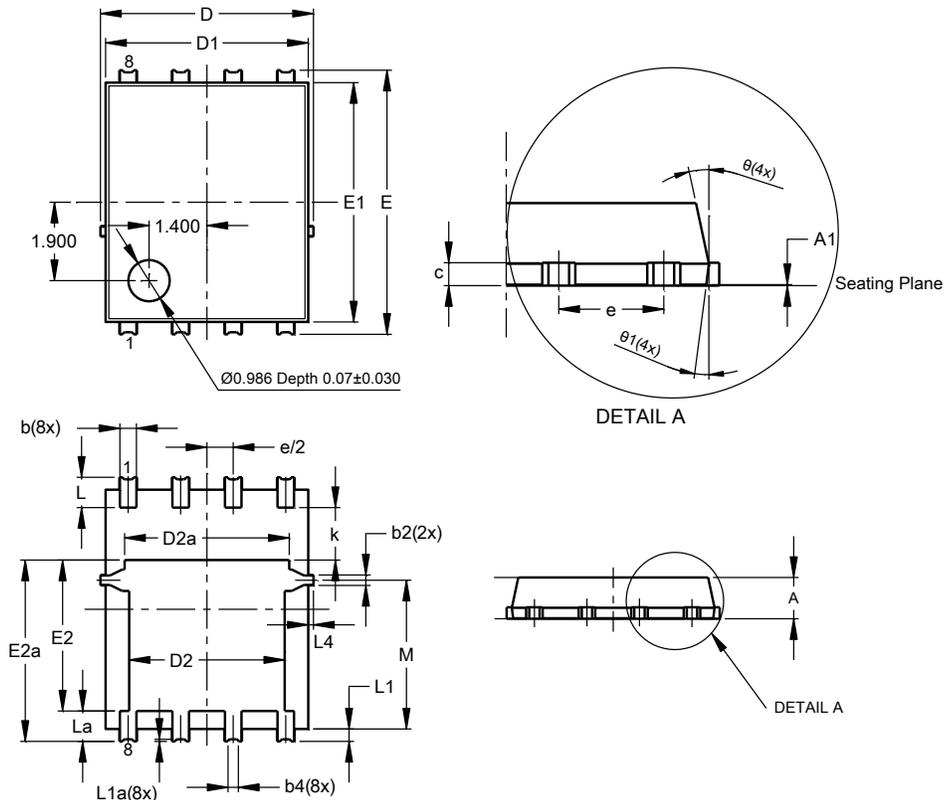


Figure 12. Transient Thermal Resistance

Package Outline Dimensions

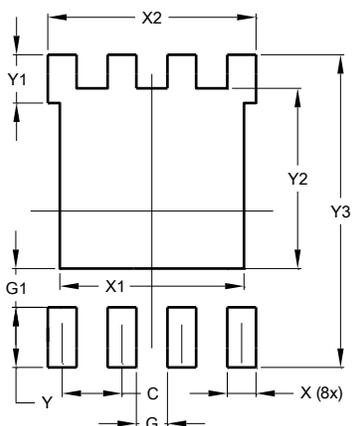
PowerDI5060-8 (SWP) (Type Q)



PowerDI5060-8 (SWP) (Type Q)			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0	0.05	--
b	0.30	0.50	0.41
b2	0.20	0.35	0.25
b4	0.25REF		
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.56	3.96	3.76
D2a	3.78	4.18	3.98
E	6.40 BSC		
E1	5.60	6.00	5.80
E2	3.46	3.86	3.66
E2a	4.195	4.595	4.395
e	1.27BSC		
k	1.05	--	--
L	0.635	0.835	0.735
La	0.635	0.835	0.735
L1	0.200	0.400	0.300
L1a	0.050REF		
L4	0.025	0.225	0.125
M	3.205	4.005	3.605
θ	10°	12°	11°
θ1	6°	8°	7°
All Dimensions in mm			

Suggested Pad Layout

PowerDI5060-8 (SWP) (Type Q)



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	4.420
Y	1.270
Y1	1.020
Y2	3.810
Y3	6.610